Vishay Semiconductors

Thyristor High Voltage, Phase Control SCR, 25 A



PRIMARY CHARACTERISTICS		
I _{T(AV)}	16 A	
V _{DRM} /V _{RRM}	800 V, 1200 V	
V _{TM}	1.25 V	
I _{GT}	45 mA	
TJ	-40 °C to 125 °C	
Package	TO-220AB 3L	
Circuit configuration	Single SCR	

FEATURES

- Designed and qualified according to JEDEC[®]-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

• Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-25TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

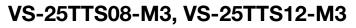
OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
Capacitive input filter $T_A = 55 \text{ °C}, T_J = 125 \text{ °C},$ common heatsink of 1 °C/W	18	22	A		

MAJOR RATINGS AND CHARACTERISTICS				
PARAMETER	TEST CONDITIONS	VALUES	UNITS	
I _{T(AV)}	Sinusoidal waveform	16	٨	
I _{RMS}		25	А	
V _{RRM} /V _{DRM}		800, 1200	V	
I _{TSM}		320	А	
V _T	16 A, T _J = 25 °C	1.25	V	
dV/dt		500	V/µs	
dl/dt		150	A/µs	
TJ		-40 to +125	°C	

VOLTAGE RATINGS					
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA		
VS-25TTS08-M3	800	800	10		
VS-25TTS12-M3	1200	1200	10		

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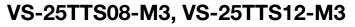
ABSOLUTE MAXIMUM RATING	5					
PARAMETER	SYMBOL	TEST CO	NDITIONS	VAL	UNITS	
PARAMETER	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS	
Maximum average on-state current	I _{T(AV)}	$T_C = 93 \ ^{\circ}C$, 180° conduction half sine wave		1	6	
Maximum RMS on-state current	I _{RMS}			2	25	Α
Maximum peak, one-cycle,		10 ms sine pulse, rated	/ _{RRM} applied	2	70	A
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no volt	age reapplied	3	20	1
Maximum 12t fay fusing	l ² t	10 ms sine pulse, rated	/ _{RRM} applied	30	65	
Maximum I ² t for fusing	I ² t	10 ms sine pulse, no volt	515		A ² s	
Maximum I²√t for fusing	l²√t	t = 0.1 to 10 ms, no voltage reapplied		51	52	A²√s
Maximum on-state voltage drop	V_{TM}	16 A, T _J = 25 °C		1.	25	V
On-state slope resistance	r _t	T 105 %O		12	2.0	mΩ
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1	.0	V
	1 /1	T _J = 25 °C		0	.5	
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	$V_{R} = Rated V_{RRM}/V_{DRM}$	1	0	
Holding current	Ι _Η	Anode supply = 6 V, resi $T_J = 25 \text{ °C}$	stive load, initial $I_T = 1 A$,	-	150	mA
Maximum latching current	١L	Anode supply = 6 V, resi	stive load, T _J = 25 °C	20	00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80	°C, $V_{DRM} = R_g - k = Open$	50	00	V/µs
Maximum rate of rise of turned-on current	dl/dt			1:	50	A/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	vv	
Maximum peak positive gate current	+ I _{GM}		1.5	А	
Maximum peak negative gate voltage	- V _{GM}		10	V	
	I _{GT}	Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	60	mA	
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	45		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20		
	V _{GT}	Anode supply = 6 V, resistive load, $T_J = -10 \degree C$	2.5		
Maximum required DC gate voltage to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	2.0	V	
voltage to trigger		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	v	
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °C V Deted volve	0.25		
Maximum DC gate current not to trigger	I _{GD}	$T_J = 125 \text{ °C}, V_{DRM} = \text{Rated value}$		mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T = 125 °C	4	μs
Typical turn-off time	tq	T _J = 125 °C	110	

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THERMAL AND MECH	IANICAL S	PECIFICA	TIONS		
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to +125	°C
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.1	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque	minimum			6 (5)	kgf ⋅ cm
	maximum			12 (10)	$(lbf \cdot in)$
Marking device			Case style TO-220AB 3L	25TTS08	
Marking device			Case signe 10-220AD SL	25TTS12	

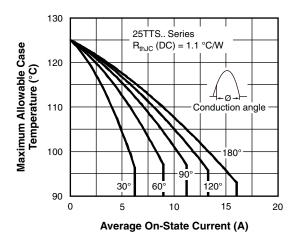
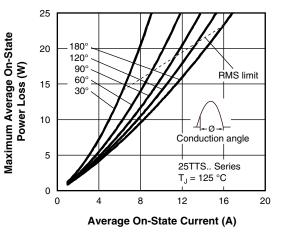
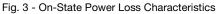


Fig. 1 - Current Rating Characteristics





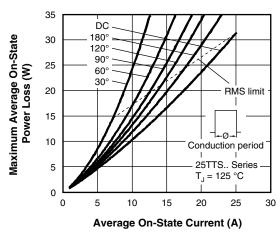
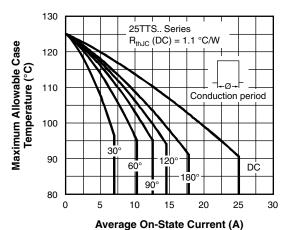


Fig. 4 - On-State Power Loss Characteristics





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VS-25TTS08-M3, VS-25TTS12-M3

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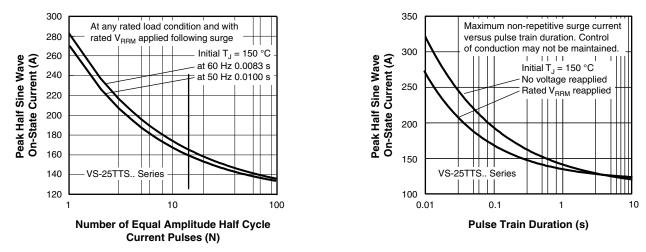


Fig. 5 - Maximum Non-Repetitive Surge Current



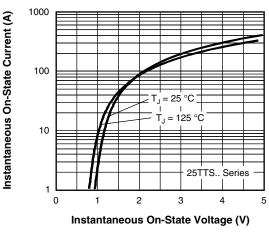
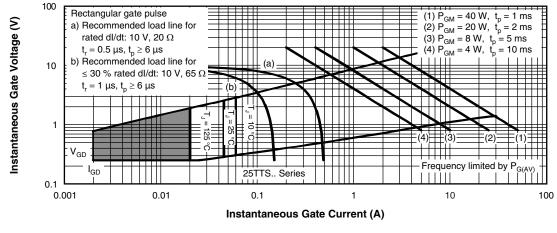


Fig. 7 - On-State Voltage Drop Characteristics





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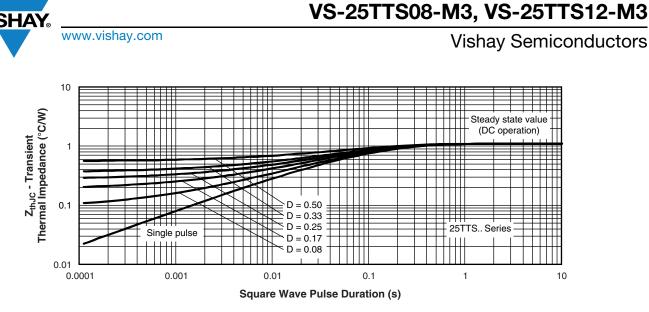


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	25	т	т	S	12	-M3	
		2	3	4	5	6	7	
	1 · 2 · 3 ·	Cur Circ T = Pac T =	rent rati uit confi single ti kage: TO-220	AB	25 A)	oduct		
	5 - 6 - 7 -	S = Volt Envi	age rati ronmen	d recove ng tal digit:			12	3 = 800 V = 1200 V terminations lead (Pb)-fi

ORDERING INFORMATION (Example)				
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION		
VS-25TTS08-M3	50	Antistatic plastic tubes		
VS-25TTS12-M3	50	Antistatic plastic tubes		

LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?96154		
Part marking information	www.vishay.com/doc?95028		

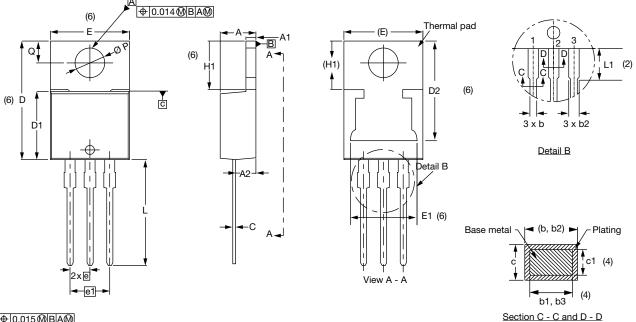
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TO-220AB 3L

DIMENSIONS in millimeters and inches



⊕0.015@BA@



Γ		
F		-

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Conforms to JEDEC[®] outline TO-220AB

Notes

⁽²⁾ Lead dimension and finish uncontrolled in L1

⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only

- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- ⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

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 $^{^{(1)}\,}$ Dimensioning and tolerancing as per ASME Y14.5M-1994 $\,$

⁽³⁾ Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁵⁾ Controlling dimensions: inches



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